

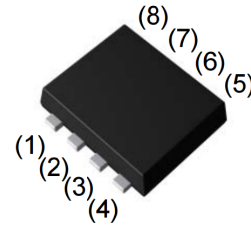
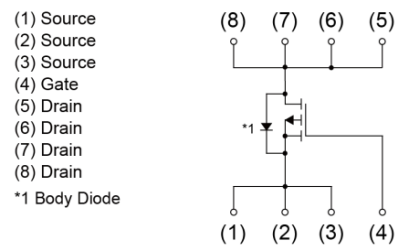
Features

- 30V/-45A,
 - $R_{DS(ON)} = 12m\Omega(\text{max.}) @ V_{GS} = -10V$
 - $R_{DS(ON)} = 17m\Omega(\text{max.}) @ V_{GS} = -6V$
 - $R_{DS(ON)} = 21m\Omega(\text{max.}) @ V_{GS} = -4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

Product Summary


DFN5X6A-8_EP


Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit	
V_{DSS}	Drain-Source Voltage	-30	V	
V_{GSS}	Gate-Source Voltage	± 25		
I_D^a	Continuous Drain Current ($V_{GS} = -10V$)	$T_A = 25^\circ\text{C}$	-15	A
		$T_A = 70^\circ\text{C}$	-12	
I_{DM}^a	300 μs Pulsed Drain Current ($V_{GS} = -10V$)	-60		
I_D^c	Continuous Drain Current ($V_{GS} = -10V$)	$T_C = 25^\circ\text{C}$	-45	
		$T_C = 100^\circ\text{C}$	-26	
I_S^a	Diode Continuous Forward Current	-4		
I_{AS}^b	Avalanche Current, Single pulse ($L = 0.3mH$)	-26		
E_{AS}^b	Avalanche Energy, Single pulse ($L = 0.3mH$)	101	mJ	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55 to 150		
P_D^a	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	4.2	W
		$T_A = 70^\circ\text{C}$	2.7	
P_D^c	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	31	
		$T_C = 100^\circ\text{C}$	12.5	
$R_{\theta JA}^a$	Thermal Resistance-Junction to Ambient	$t \leq 10s$	30	$^\circ\text{C/W}$
		Steady State	65	
$R_{\theta JC}^c$	Thermal Resistance-Junction to Case	Steady State	4	

Note a : Surface Mounted on $1in^2$ pad area, $t \leq 10sec$.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J = 25^\circ\text{C}$).

Note c : The power dissipation P_D is based on $T_{J(MAX)} = 150^\circ\text{C}$, and it is useful for reducing junction-to-case thermal resistance ($R_{\theta JC}$) when additional heat sink is used.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

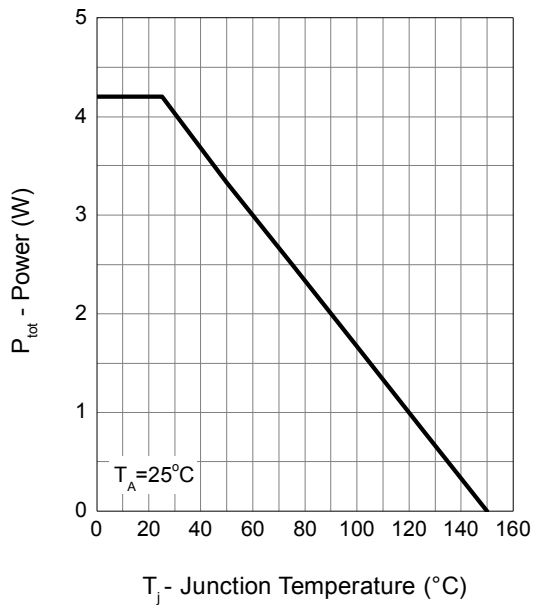
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=-250\mu A$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	μA
		$T_J=85^\circ C$	-	-	-30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-1.5	-2	-2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$	-	-	± 100	nA
$R_{DS(ON)}^d$	Drain-Source On-state Resistance	$V_{GS}=-10V, I_{DS}=-15A$	-	9.6	12	m Ω
		$V_{GS}=-6V, I_{DS}=-10A$	-	13	17	
		$V_{GS}=-4.5V, I_{DS}=-5A$	-	15	21	
Diode Characteristics						
V_{SD}^d	Diode Forward Voltage	$I_{SD}=-1A, V_{GS}=0V$	-	-0.7	-1	V
t_{rr}^e	Reverse Recovery Time	$I_{SD}=-15A, di_{SD}/dt=100A/\mu s$	-	22	-	ns
Q_{rr}^e	Reverse Recovery Charge		-	15	-	nC
Dynamic Characteristics^e						
R_g	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$	-	2	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-15V,$ Frequency=1.0MHz	-	1550	-	pF
C_{oss}	Output Capacitance		-	315	-	
C_{rss}	Reverse Transfer Capacitance		-	245	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=-15V, R_L=15\Omega,$ $I_{DS}=-1A, V_{GEN}=-10V,$ $R_G=6\Omega$	-	13	-	ns
t_r	Turn-on Rise Time		-	15	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	50	-	
t_f	Turn-off Fall Time		-	29	-	
Gate Charge Characteristics^e						
Q_g	Total Gate Charge	$V_{DS}=-15V, V_{GS}=-10V,$ $I_{DS}=-15A$	-	31	-	nC
Q_{gs}	Gate-Source Charge		-	4.3	-	
Q_{gd}	Gate-Drain Charge		-	10	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

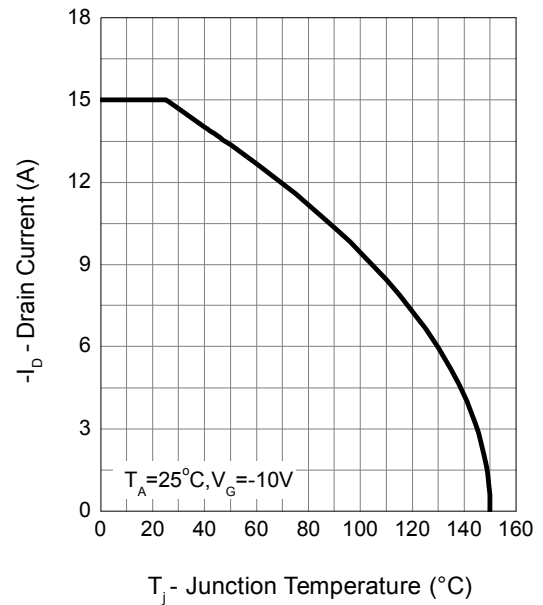
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

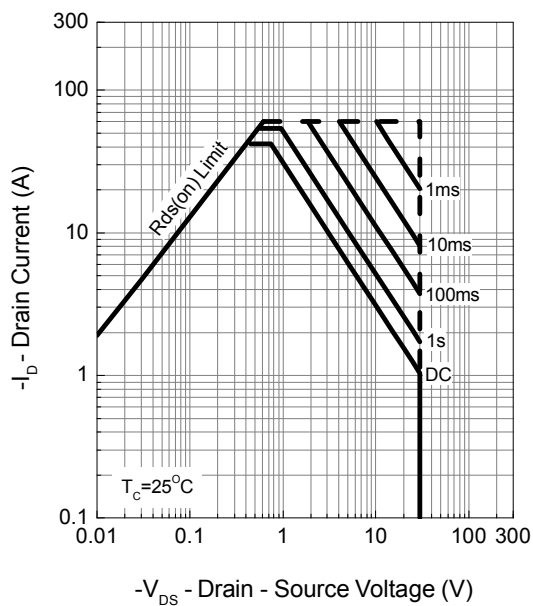
Power Dissipation



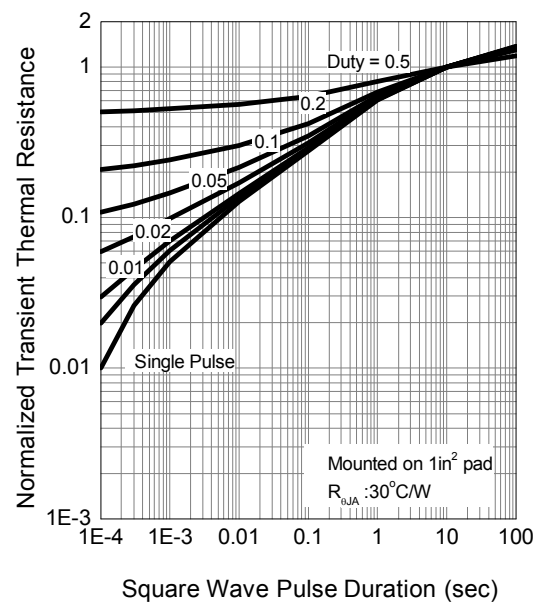
Drain Current



Safe Operation Area

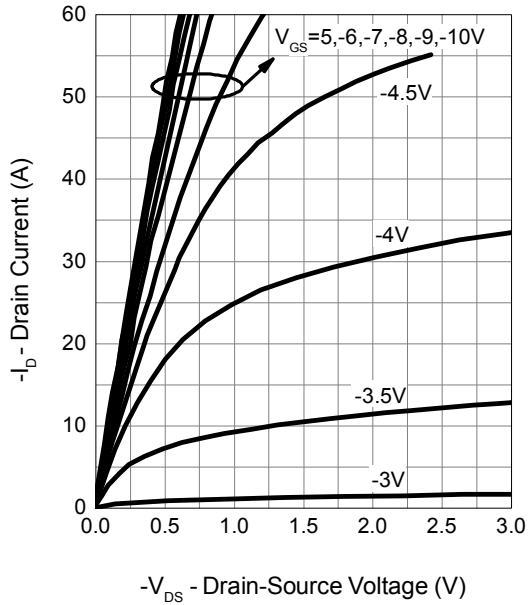


Thermal Transient Impedance

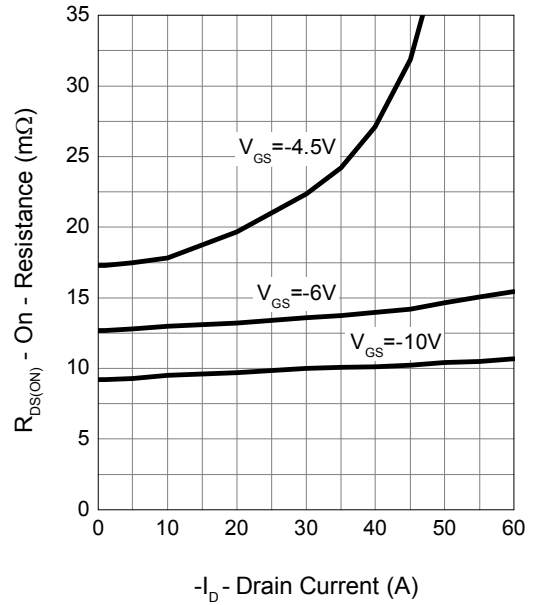


Typical Operating Characteristics (Cont.)

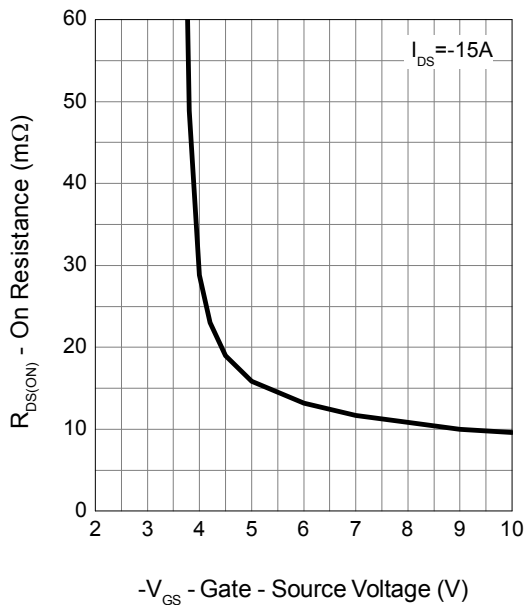
Output Characteristics



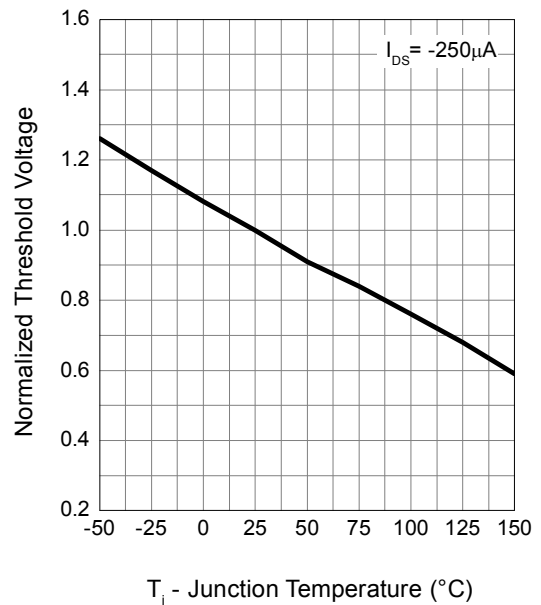
Drain-Source On Resistance



Gate-Source On Resistance

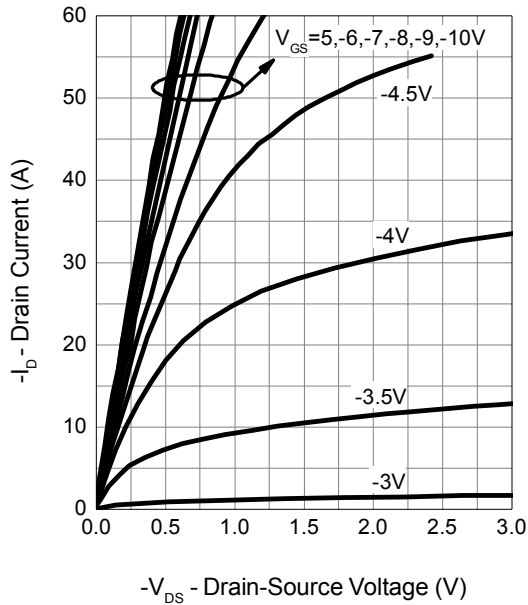


Gate Threshold Voltage

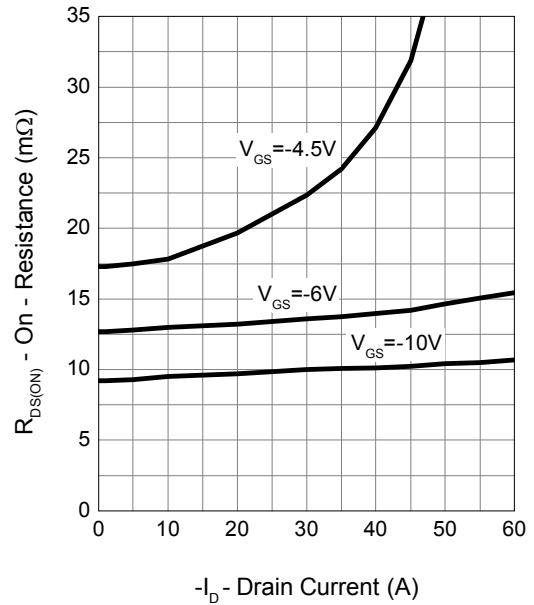


Typical Operating Characteristics (Cont.)

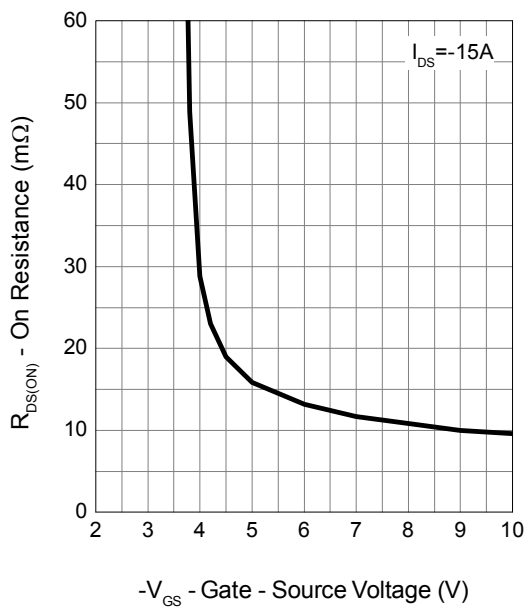
Output Characteristics



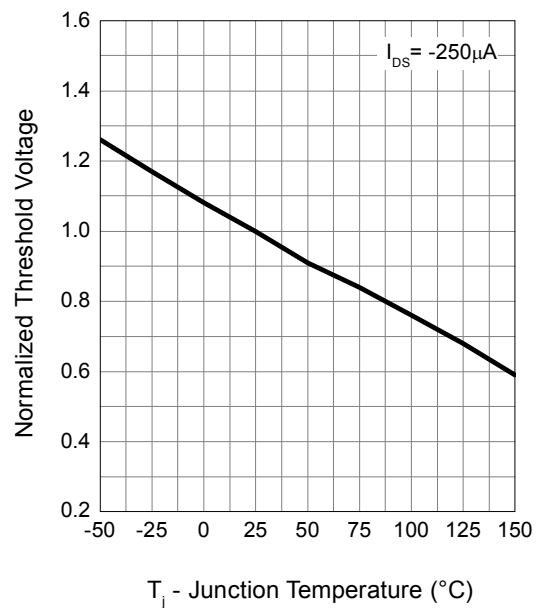
Drain-Source On Resistance



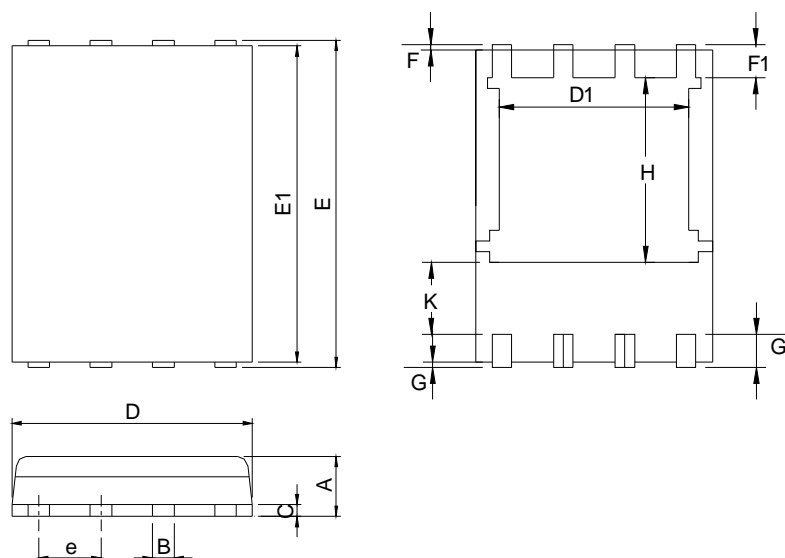
Gate-Source On Resistance



Gate Threshold Voltage

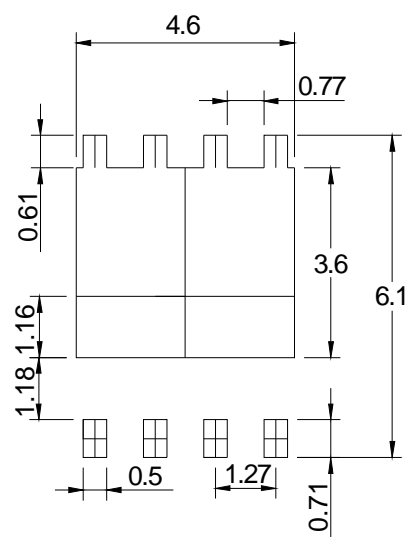


Package Information



SYMBOL	DFN5x6A-8_EP			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.20	0.035	0.047
B	0.3	0.51	0.012	0.020
C	0.19	0.25	0.007	0.010
D	4.80	5.30	0.189	0.209
D1	4.00	4.40	0.157	0.173
E	5.90	6.20	0.232	0.244
E1	5.50	5.80	0.217	0.228
e	1.27 BSC		0.050 BSC	
F	0.05	0.30	0.002	0.012
F1	0.35	0.75	0.014	0.030
G	0.05	0.30	0.002	0.012
G1	0.35	0.75	0.014	0.030
H	3.34	3.9	0.131	0.154
K	0.762	-	0.03	-

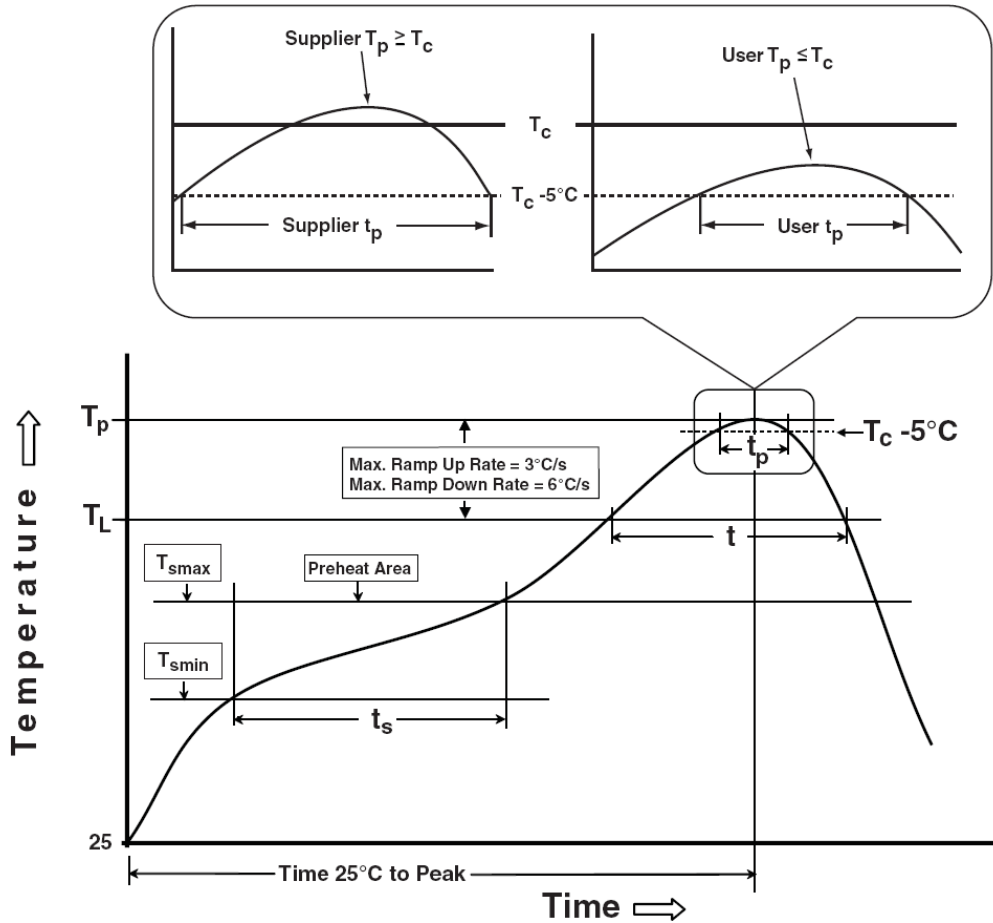
RECOMMENDED LAND PATTERN



UNIT: mm

Note : 1.Dimension D, D1,D2 and E1 do not include mold flash or protrusions.
Mold flash or protrusions shall not exceed 10 mil.

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Attention

- 1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.
- 2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.
- 3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- 4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- 5, In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- 6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.
- 7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- 8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you intend to use.
- 9, this catalog provides information as of Sep. 2014. Specifications and information herein are subject to change without notice.

单击下面可查看定价，库存，交付和生命周期等信息

[>>WINSOK\(微硕\)](#)